

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6,380,029").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/16 09:20
L2	0	(etching same tungsten near silicide same second near polysilicon and annealing same tungsten near silicide and gate near electrode). clm.	US-PGPUB; USPAT	OR	OFF	2006/11/16 09:22